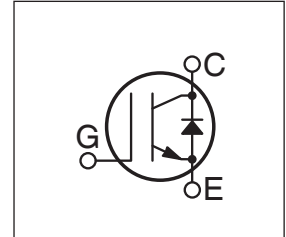
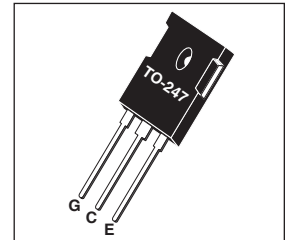


POWER MOS 7® IGBT

The POWER MOS 7® IGBT is a new generation of high voltage power IGBTs. Using Punch Through Technology this IGBT is ideal for many high frequency, high voltage switching applications and has been optimized for high frequency switchmode power supplies.

- Low Conduction Loss
- Low Gate Charge
- Ultrafast Tail Current shutoff
- 100 kHz operation @ 600V, 10A
- 50 kHz operation @ 600V, 16A
- RBSOA Rated




MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	APT13GP120BDQ1(G)	UNIT
V_{CES}	Collector-Emitter Voltage	1200	Volts
V_{GE}	Gate-Emitter Voltage	± 20	
I_{C1}	Continuous Collector Current @ $T_C = 25^\circ\text{C}$	41	Amps
I_{C2}	Continuous Collector Current @ $T_C = 110^\circ\text{C}$	20	
I_{CM}	Pulsed Collector Current ^① @ $T_C = 150^\circ\text{C}$	50	
RBSOA	Reverse Bias Safe Operating Area @ $T_j = 150^\circ\text{C}$	50A @ 960V	
P_D	Total Power Dissipation	250	Watts
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$
T_L	Max. Lead Temp. for Soldering: 0.063" from Case for 10 Sec.	300	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	Units
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage ($V_{GE} = 0V, I_C = 500\mu\text{A}$)	1200			Volts
$V_{GE(TH)}$	Gate Threshold Voltage ($V_{CE} = V_{GE}, I_C = 1\text{mA}, T_j = 25^\circ\text{C}$)	3	4.5	6	
$V_{CE(ON)}$	Collector-Emitter On Voltage ($V_{GE} = 15V, I_C = 13A, T_j = 25^\circ\text{C}$)		3.3	3.9	
	Collector-Emitter On Voltage ($V_{GE} = 15V, I_C = 13A, T_j = 125^\circ\text{C}$)		3.0		
I_{CES}	Collector Cut-off Current ($V_{CE} = 1200V, V_{GE} = 0V, T_j = 25^\circ\text{C}$) ^②			500	μA
	Collector Cut-off Current ($V_{CE} = 1200V, V_{GE} = 0V, T_j = 125^\circ\text{C}$) ^②			3000	
I_{GES}	Gate-Emitter Leakage Current ($V_{GE} = \pm 20V$)			± 100	nA

 **CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

DYNAMIC CHARACTERISTICS

APT13GP120BDQ1(G)

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT	
C_{ies}	Input Capacitance	Capacitance $V_{GE} = 0V, V_{CE} = 25V$ $f = 1 \text{ MHz}$		1145		pF	
C_{oes}	Output Capacitance			90			
C_{res}	Reverse Transfer Capacitance			15			
V_{GEP}	Gate-to-Emitter Plateau Voltage	Gate Charge		7.5		V	
Q_g	Total Gate Charge ⁽³⁾	$V_{GE} = 15V$		55		nC	
Q_{ge}	Gate-Emitter Charge	$V_{CE} = 600V$		8			
Q_{gc}	Gate-Collector ("Miller") Charge	$I_C = 13A$		26			
SSOA	Switching Safe Operating Area	$T_J = 150^\circ C, R_G = 5\Omega, V_{GE} = 15V, L = 100\mu H, V_{CE} = 960V$	50			A	
$t_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{CC} = 600V$ $V_{GE} = 15V$ $I_C = 13A$ $R_G = 5\Omega$ $T_J = +25^\circ C$		9		ns	
t_r	Current Rise Time			12			
$t_{d(off)}$	Turn-off Delay Time			28			
t_f	Current Fall Time			34			
E_{on1}	Turn-on Switching Energy ⁽⁴⁾			115			μJ
E_{on2}	Turn-on Switching Energy (Diode) ⁽⁵⁾		330				
E_{off}	Turn-off Switching Energy ⁽⁶⁾		165				
$t_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{CC} = 600V$ $V_{GE} = 15V$ $I_C = 13A$ $R_G = 5\Omega$ $T_J = +125^\circ C$		9		ns	
t_r	Current Rise Time			12			
$t_{d(off)}$	Turn-off Delay Time			70			
t_f	Current Fall Time			200			
E_{on1}	Turn-on Switching Energy ⁽⁴⁾			225			μJ
E_{on2}	Turn-on Switching Energy (Diode) ⁽⁵⁾			710			
E_{off}	Turn-off Switching Energy ⁽⁶⁾			840			

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case (IGBT)			.50	°C/W
$R_{\theta JC}$	Junction to Case (DIODE)			1.18	
W_T	Package Weight		5.9		gm

① Repetitive Rating: Pulse width limited by maximum junction temperature.

② For Combi devices, I_{ces} includes both IGBT and FRED leakages

③ See MIL-STD-750 Method 3471.

④ E_{on1} is the clamped inductive turn-on-energy of the IGBT only, without the effect of a commutating diode reverse recovery current adding to the IGBT turn-on loss. (See Figure 24.)

⑤ E_{on2} is the clamped inductive turn-on energy that includes a commutating diode reverse recovery current in the IGBT turn-on switching loss. (See Figures 21, 22.)

⑥ E_{off} is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1. (See Figures 21, 23.)

APT Reserves the right to change, without notice, the specifications and information contained herein.

TYPICAL PERFORMANCE CURVES

APT13GP120BDQ1(G)

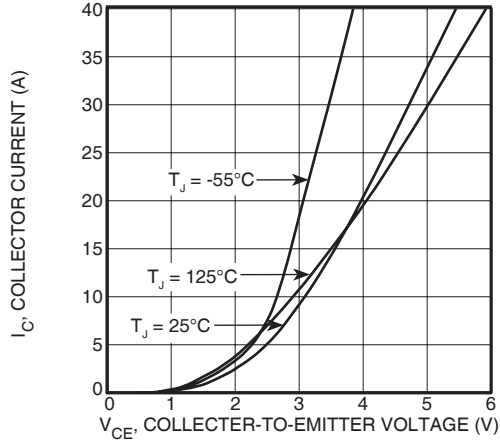


FIGURE 1, Output Characteristics($T_J = 25^\circ\text{C}$)

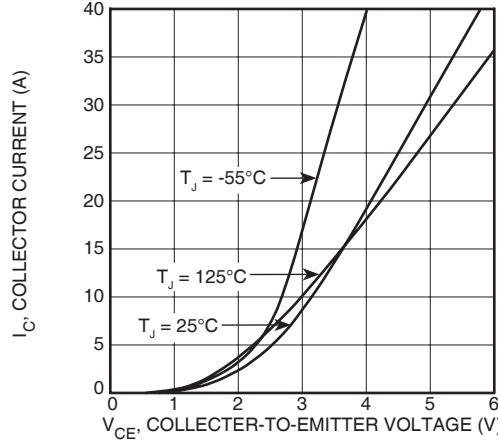


FIGURE 2, Output Characteristics ($T_J = 125^\circ\text{C}$)

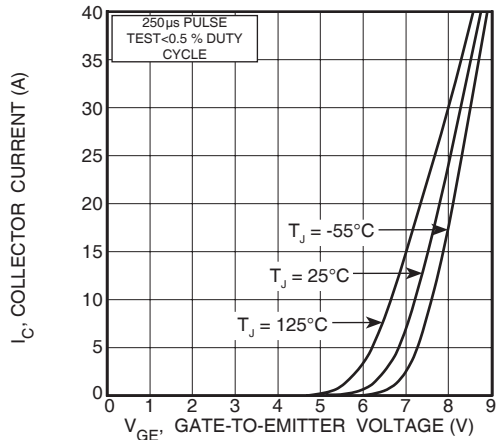


FIGURE 3, Transfer Characteristics

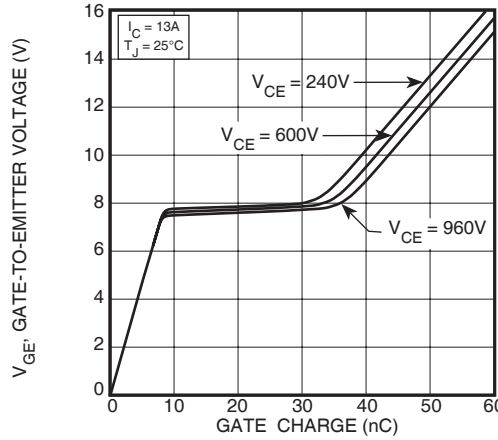


FIGURE 4, Gate Charge

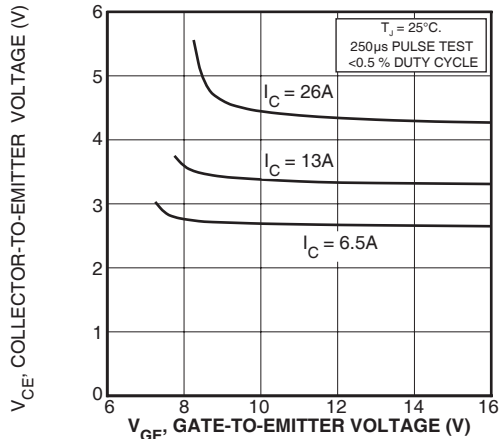


FIGURE 5, On State Voltage vs Gate-to-Emitter Voltage

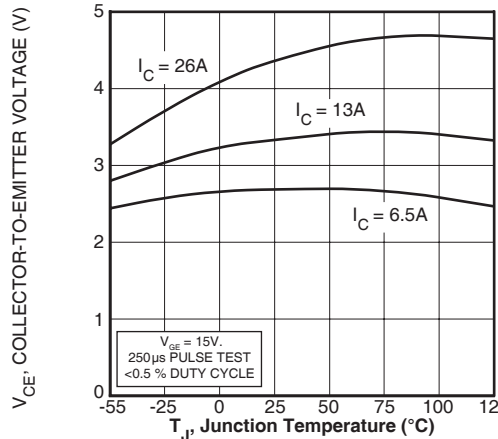


FIGURE 6, On State Voltage vs Junction Temperature

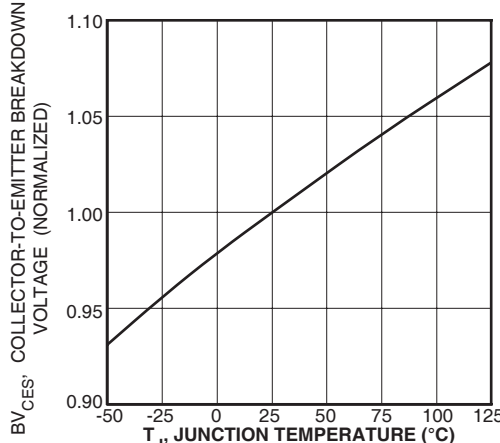


FIGURE 7, Breakdown Voltage vs. Junction Temperature

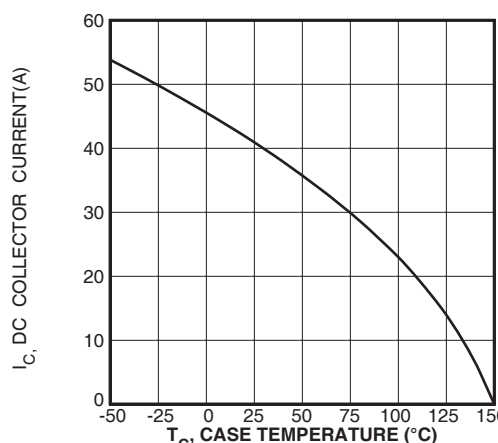


FIGURE 8, DC Collector Current vs Case Temperature

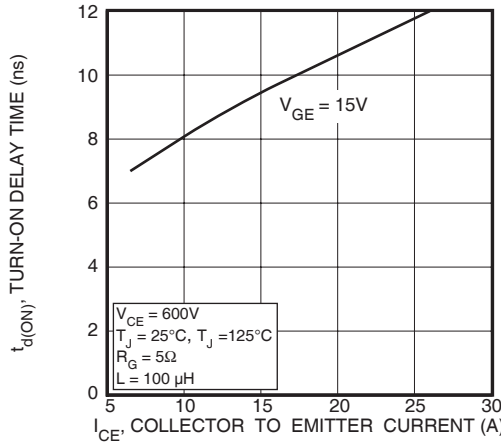


FIGURE 9, Turn-On Delay Time vs Collector Current

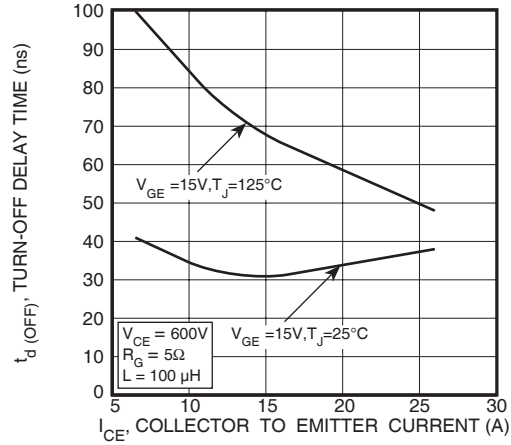


FIGURE 10, Turn-Off Delay Time vs Collector Current

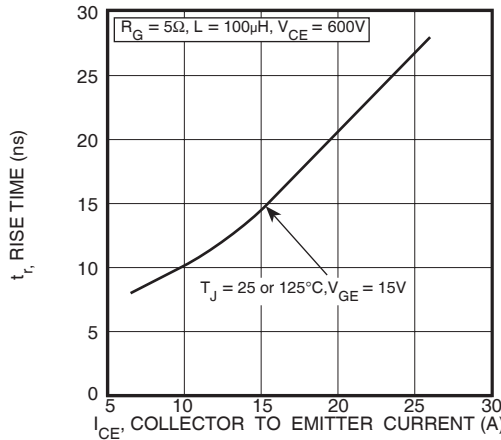


FIGURE 11, Current Rise Time vs Collector Current

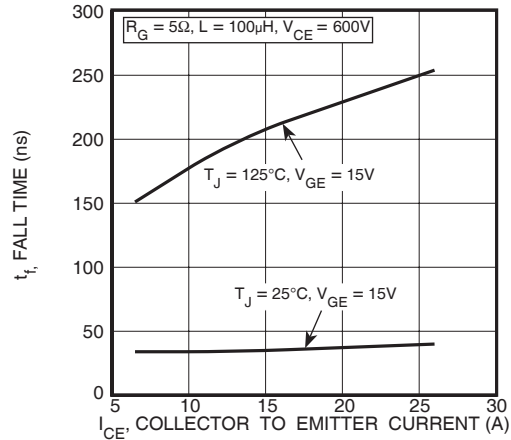


FIGURE 12, Current Fall Time vs Collector Current

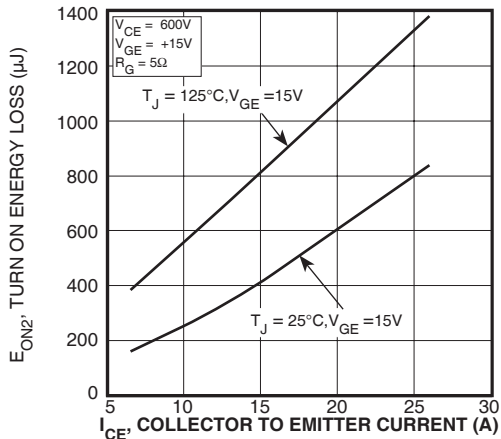


FIGURE 13, Turn-On Energy Loss vs Collector Current

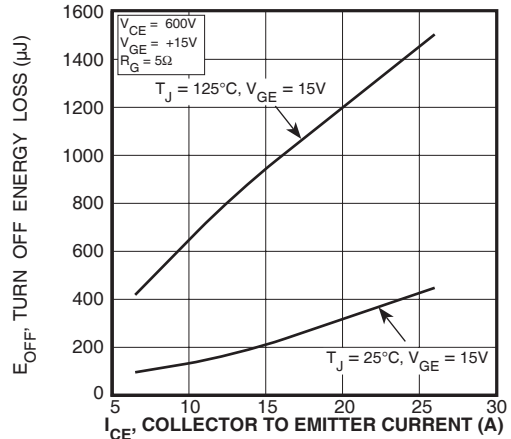


FIGURE 14, Turn Off Energy Loss vs Collector Current

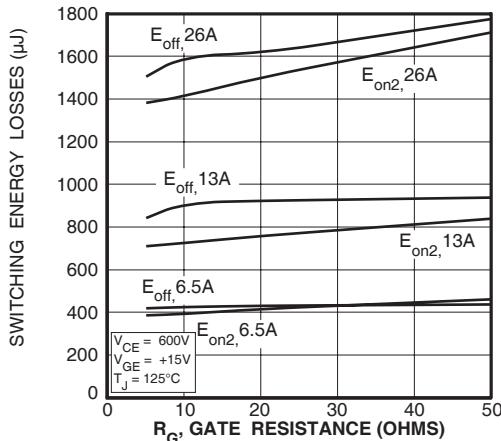


FIGURE 15, Switching Energy Losses vs. Gate Resistance

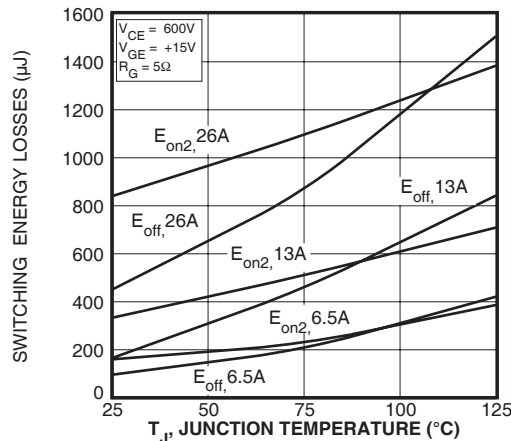


FIGURE 16, Switching Energy Losses vs Junction Temperature

TYPICAL PERFORMANCE CURVES

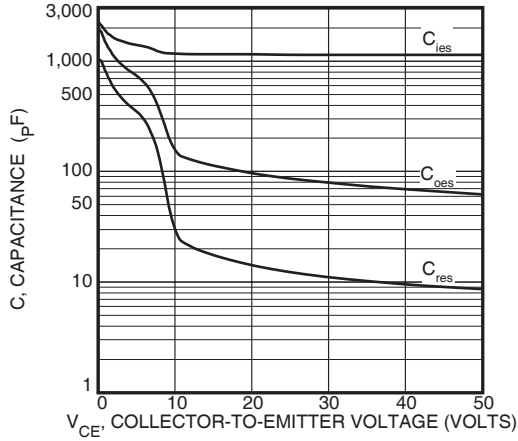


Figure 17, Capacitance vs Collector-To-Emitter Voltage

APT13GP120BDQ1(G)

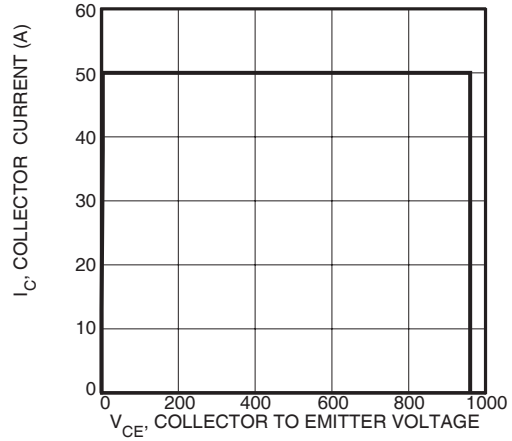


Figure 18, Minimum Switching Safe Operating Area

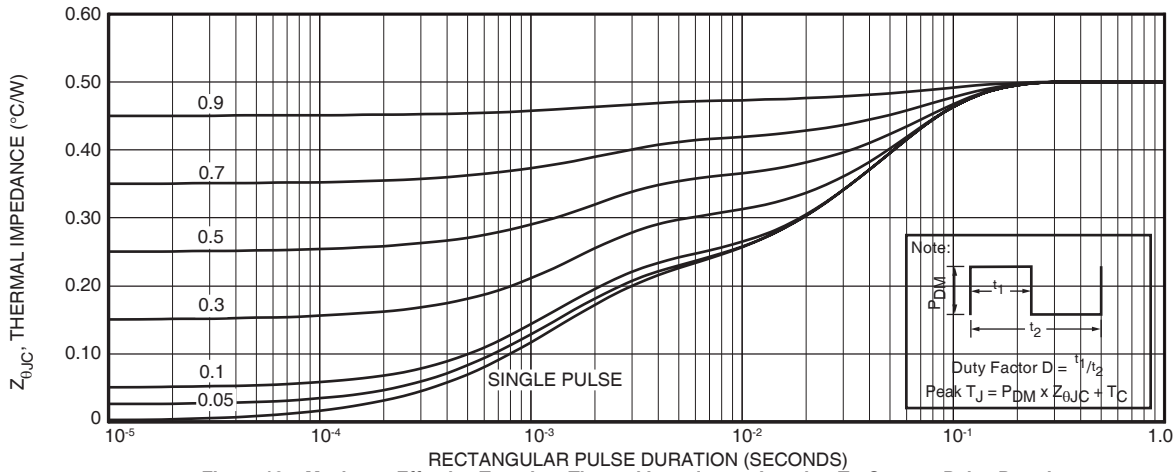


Figure 19a, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

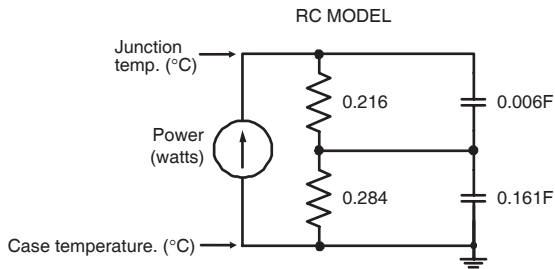


FIGURE 19b, TRANSIENT THERMAL IMPEDANCE MODEL

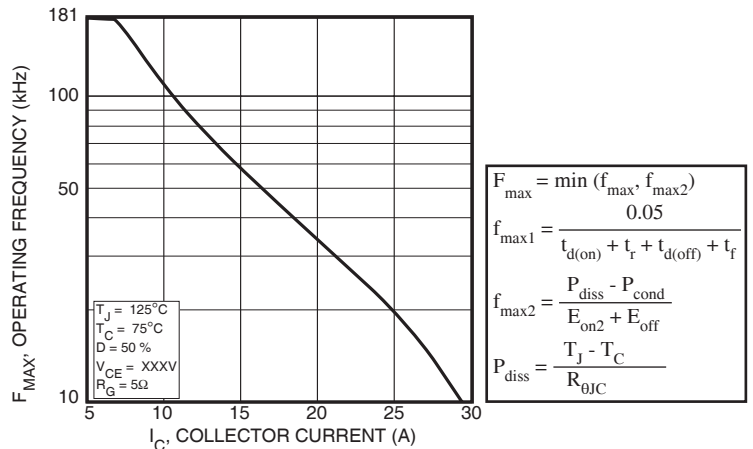


Figure 20, Operating Frequency vs Collector Current

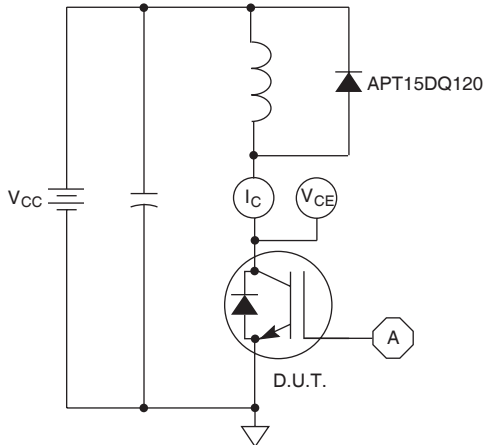


Figure 21, Inductive Switching Test Circuit

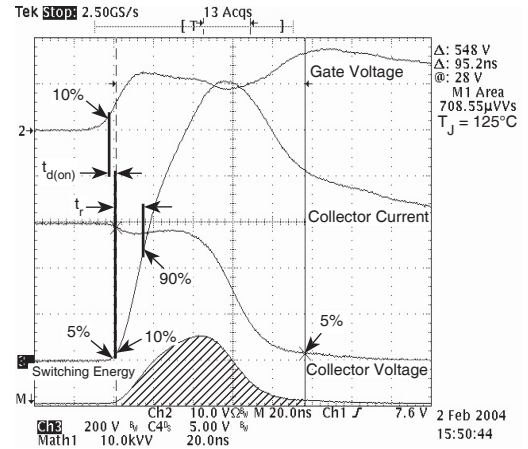


Figure 22, Turn-on Switching Waveforms and Definitions

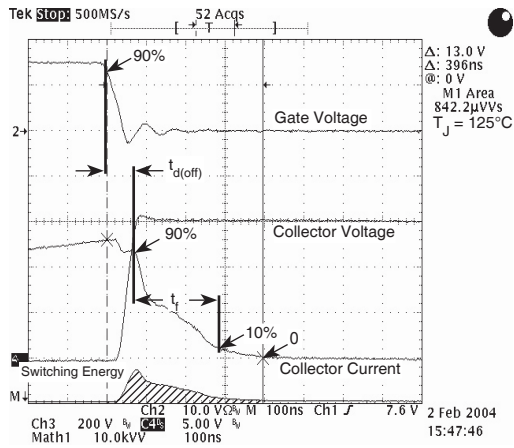


Figure 23, Turn-off Switching Waveforms and Definitions

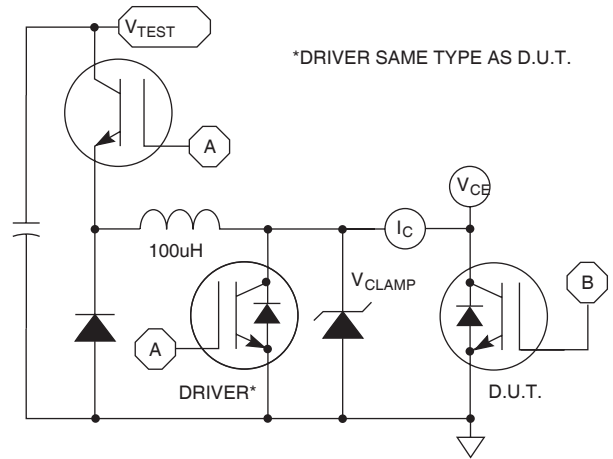


Figure 24, EON1 Test Circuit

ULTRAFAST SOFT RECOVERY ANTI-PARALLEL DIODE

MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Characteristic / Test Conditions	APT13GP120BDQ1(G)		UNIT
$I_F(AV)$	Maximum Average Forward Current ($T_C = 127^\circ\text{C}$, Duty Cycle = 0.5)	15		Amps
$I_F(RMS)$	RMS Forward Current (Square wave, 50% duty)	29		
I_{FSM}	Non-Repetitive Forward Surge Current ($T_J = 45^\circ\text{C}$, 8.3ms)	110		

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
V_F	Forward Voltage	$I_F = 13A$	2.7		Volts
		$I_F = 26A$	3.3		
		$I_F = 13A, T_J = 125^\circ\text{C}$	2.3		

DYNAMIC CHARACTERISTICS

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
t_{rr}	Reverse Recovery Time	$I_F = 1A, di_F/dt = -100A/\mu s, V_R = 30V, T_J = 25^\circ\text{C}$	-	21		ns
t_{rr}	Reverse Recovery Time	$I_F = 15A, di_F/dt = -200A/\mu s, V_R = 800V, T_C = 25^\circ\text{C}$	-	240		
Q_{rr}	Reverse Recovery Charge		-	260		nC
I_{RRM}	Maximum Reverse Recovery Current		-	3	-	Amps
t_{rr}	Reverse Recovery Time	$I_F = 15A, di_F/dt = -200A/\mu s, V_R = 800V, T_C = 125^\circ\text{C}$	-	290		ns
Q_{rr}	Reverse Recovery Charge		-	960		nC
I_{RRM}	Maximum Reverse Recovery Current		-	6	-	Amps
t_{rr}	Reverse Recovery Time	$I_F = 15A, di_F/dt = -1000A/\mu s, V_R = 800V, T_C = 125^\circ\text{C}$	-	130		ns
Q_{rr}	Reverse Recovery Charge		-	1340		nC
I_{RRM}	Maximum Reverse Recovery Current		-	19		Amps

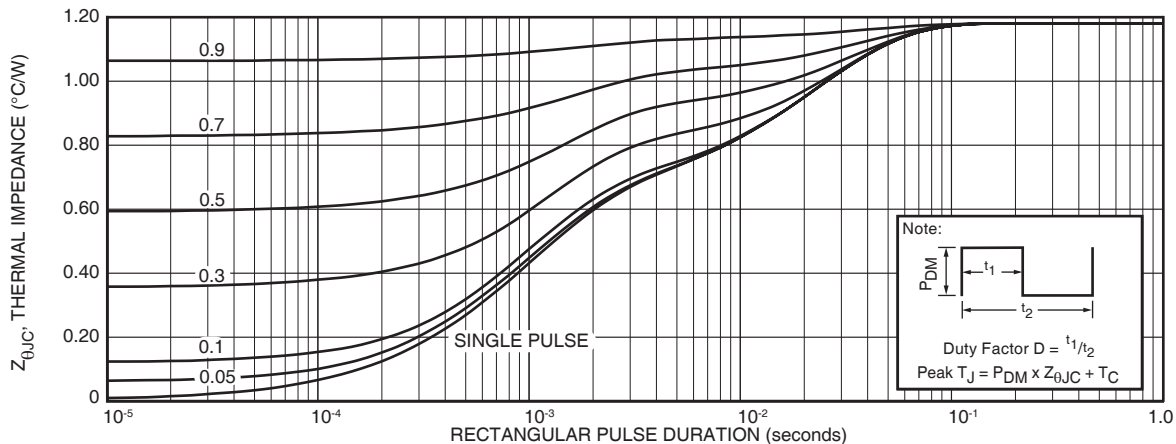


FIGURE 25a. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION



FIGURE 25b. TRANSIENT THERMAL IMPEDANCE MODEL

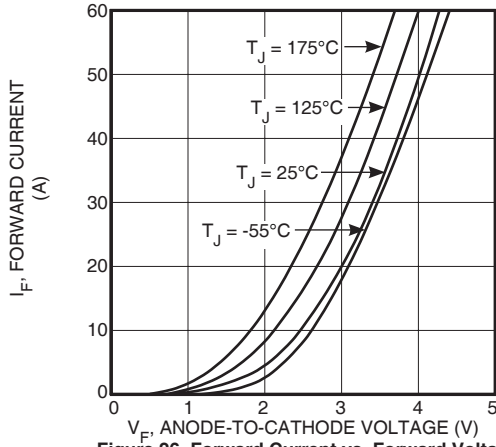


Figure 26. Forward Current vs. Forward Voltage

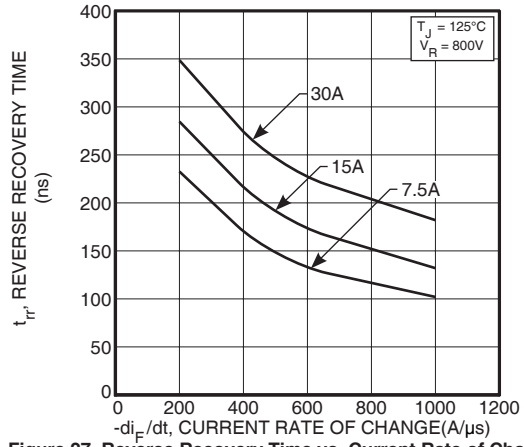


Figure 27. Reverse Recovery Time vs. Current Rate of Change

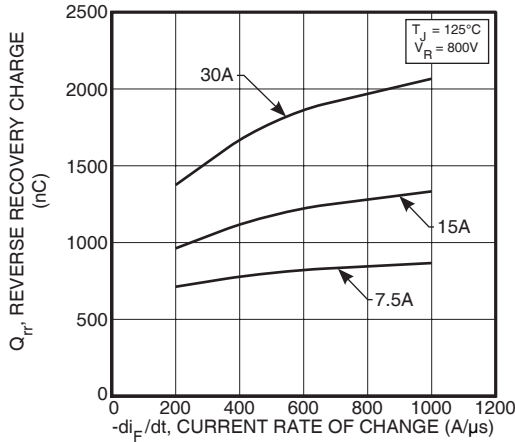


Figure 28. Reverse Recovery Charge vs. Current Rate of Change

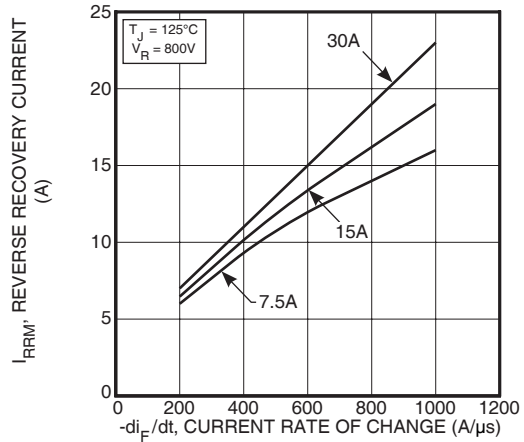


Figure 29. Reverse Recovery Current vs. Current Rate of Change



Figure 30. Dynamic Parameters vs. Junction Temperature



Figure 31. Maximum Average Forward Current vs. Case Temperature

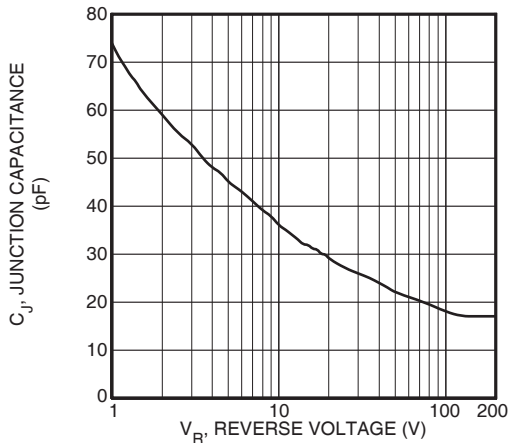


Figure 32. Junction Capacitance vs. Reverse Voltage

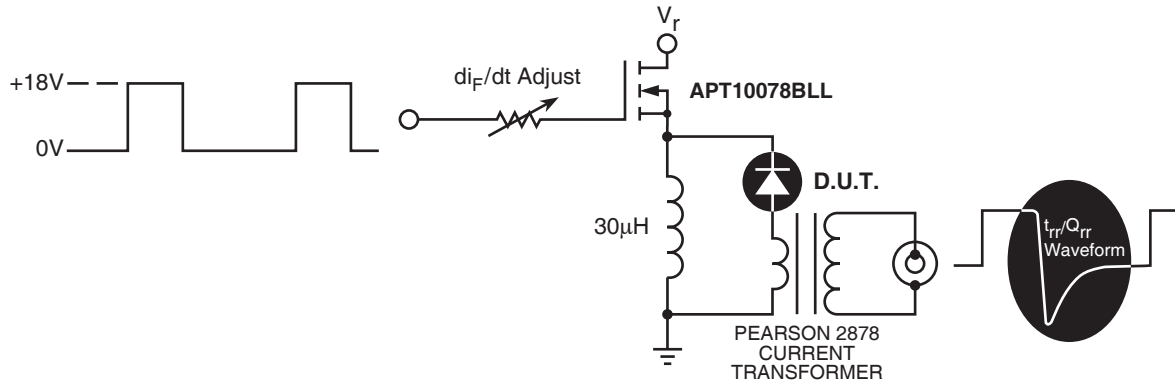


Figure 33. Diode Test Circuit

- 1 I_F - Forward Conduction Current
- 2 di_F/dt - Rate of Diode Current Change Through Zero Crossing.
- 3 I_{RRM} - Maximum Reverse Recovery Current.
- 4 t_{rr} - Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and $0.25 \cdot I_{RRM}$ passes through zero.
- 5 Q_{rr} - Area Under the Curve Defined by I_{RRM} and t_{rr} .

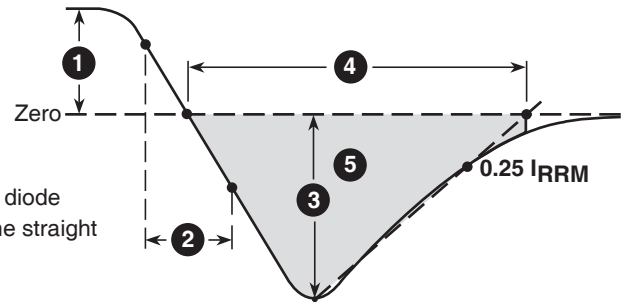


Figure 34, Diode Reverse Recovery Waveform and Definitions

TO-247 Package Outline

ⓔ1 SAC: Tin, Silver, Copper



Dimensions in Millimeters and (Inches)

APT's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. US and Foreign patents pending. All Rights Reserved.

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9